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APPENDIX

TABLE SI. The energy difference between spin-polarized (along [001] and [100], respectively) and non-spin-polarized as well as energy difference between FM and AFM configurations as a function of Hubbard U.

U (eV)	$E_{[001]}$ - E_{NSP} (eV)	$E_{[001]}$ - E_{NSP} (eV)	E_{AFM} - E_{FM} (meV)
0.5	-4.439	-4.439	78.165
1.0	-4.984	-4.984	85.989
2.0	-5.897	-5.897	97.992
3.0	-6.603	-6.602	106.546



FIG. S1 (a, b) Top and side views of FE ML-Sc₂CO₂. The pink, light purple and dark blue balls represent Sc, C and O atoms, respectively. (c) The energy band structure.



FIG. S2 (a, b) Atomic-resolved band structures of ML-CGT, where the olive, violet and orange symbols denote Cr, Ge, and Te atoms, respectively. The size of the symbols represents the weight of atoms. The Fermi level is set to zero in energy.

TABLE SII. The matrix differences of Cr-*d* between magnetization along *z* and *x* in Eqs. (3) and (4).

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FIG. S3. (a) Temperature-dependent magnetic moment and specific heat for ML-CGT based on MC simulations. (b) Five spin configurations, named AFM1, AFM2, AFM3, AFM4, FM. (c) J under different spin configurations, where J_I is the nearest exchange interaction when only two configurations are considered.



FIG. S4. (a) The bonding angles and (b) Cr-I bonding length (L_{Cr-I}) and Cr-Cr distance (L_{Cr-Cr}) in ML-CrI₃ under compressive (negative sign) and tensile (positive sign) strains, respectively.



FIG. S5. Three types of defects including Cr, Ge, and Te in ML-CGT and their band structures are shown respectively. The red line represents the energy bands with spin-up, and the blue line represents the energy bands with spin-down. The circles represent the atomic vacancy positions.

TABLE SIII. The formation energy for point defects and change of atomic spin magnetic moments. The formation energy of defects is calculated using the following expression:

$$\Delta E_f = E_V - E_{total} + \sum_{\alpha} n_{\alpha} \mu_{\alpha}$$

where E_V and E_{total} are the total energies of ML-CGT with and without atomic vacancies, respectively. μ_{α} is the absolute value of the chemical potential of atom α , and n_{α} is the number of such defect atoms; $n_{\alpha} = -1$ if an atom is added, $n_{\alpha} = 1$ while if an atom is removed.

 $\Delta E_f(eV) \qquad m_s^{Cr}(\mu_B/atom) \qquad m_s^{Ge}(\mu_B/atom) \qquad m_s^{Te}(\mu_B/atom)$

-	Cr ₇ Ge ₈ Te ₂₄	3.273	3.268	0.024	-0.159
	$Cr_6Ge_8Te_{24}$	6.504	3.250	0.023	-0.153
	$Cr_8Ge_7Te_{24}$	3.063	3.262	0.033	-0.158
	Cr ₈ Ge ₆ Te ₂₄	6.092	3.236	0.033	-0.176
	Cr ₈ Ge ₈ Te ₂₃	2.209	3.346	0.014	-0.132
	$Cr_8Ge_8Te_{22}$	4.449	3.396	-0.005	-0.141



Fig. S6 (a, b, c, d) represent the energy bands of CGT/P \uparrow at different Hubbard U, where red and blue indicates spinup and spin-down channels, respectively. (e, f, g, h) represent the energy band components of CGT at different Hubbard U.



FIG. S7. (a) Band changes after gradually adding electrons to ML-CGT. (b) The energy band structure of CGT/Sc₂CO₂ (P \uparrow). The red line represents the energy bands with spin-up, and the blue line represents the energy bands with spin-down. We can find that the effect of Sc₂CO₂ (P \uparrow) on ML-CGT is equivalent to the injection of electrons.



FIG. S8. (a, b) Side views of CGT/In₂Se₃ HTS with FE dipole moment directed upward and downward ($P\downarrow$ and $P\uparrow$), respectively, (c, d) The energy band structure of CGT/In₂Se₃. The red line represents the energy bands with spin-up, and the blue line represents the energy bands with spin-down. (e, f) Layer-resolved band structures of CGT/In₂Se₃, where the olive and orange symbols denote In₂Se₃ and CGT, respectively.